

HiPerFRED Module

 $V_{RRM} = 400 V$

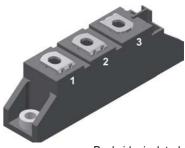
 $I_{\text{FAV}} = 2x \ 150 \text{ A}$

 $t_{rr} = 40 \, \text{ns}$

Common Cathode

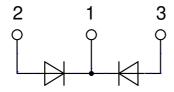
Part number

MEK150-04DA



Backside: isolated





Features / Advantages:

- Planar passivated chips
- Low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
- Power dissipation within the diode
- Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

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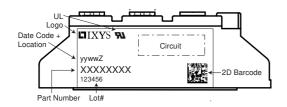


Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocki	$T_{VJ} = 25^{\circ}C$			400	V	
V _{RRM}	max. repetitive reverse blocking voltage		$T_{VJ} = 25^{\circ}C$			400	V
IR	reverse current, drain current	$V_R = 400 \text{ V}$	$T_{VJ} = 25^{\circ}C$			2	mA
		$V_R = 400 \text{ V}$	$T_{VJ} = 150^{\circ}C$			8,5	mA
V _F	forward voltage drop	I _F = 150 A	$T_{VJ} = 25^{\circ}C$			1,35	V
		$I_F = 300 \text{ A}$				1,63	٧
		I _F = 150 A	T _{VJ} = 150°C			1,09	٧
		$I_F = 300 A$				1,41	٧
I _{FAV}	average forward current	T _C = 100°C	$T_{VJ} = 175$ °C			150	Α
		rectangular d = 0.5					i ! !
V _{F0}	threshold voltage		$T_{VJ} = 175$ °C			0,73	٧
\mathbf{r}_{F}	slope resistance for power loss calculation only					2	mΩ
R _{thJC}	thermal resistance junction to case	9				0,35	K/W
R _{thCH}	thermal resistance case to heatsink				0,08		K/W
P _{tot}	total power dissipation		$T_{C} = 25^{\circ}C$			430	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			1,20	kA
C¹	junction capacitance	$V_R = 400 V$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		220		pF
I _{RM}	max. reverse recovery current		$T_{VJ} = 25^{\circ}C$		30		Α
		$I_F = 200 \text{ A}; V_R = 200 \text{ V}$	$T_{VJ} = 100$ °C		60		Α
t _{rr}	reverse recovery time	$\begin{cases} I_F = 200 \text{ A}; V_R = 200 \text{ V} \\ -\text{di}_F/\text{dt} = 600 \text{ A}/\mu\text{s} \end{cases}$	$T_{VJ} = 25^{\circ}C$		40		ns
	,	1	$T_{VJ} = 100$ °C		90		ns





Package TO-240AA			Ratings					
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					200	Α
T _{VJ}	virtual junction temperature				-40		175	°C
Top	operation temperature				-40		150	°C
T _{stg}	storage temperature				-40		125	°C
Weight						76		g
M _D	mounting torque				2,5		4	Nm
$\mathbf{M}_{_{\mathrm{T}}}$	terminal torque				2,5		4	Nm
d _{Spp/App}	creepage distance on surface striking dist	Latriting distance through air	terminal to terminal	13,0	9,7			mm
d _{Spb/Apb}		striking distance through air	terminal to backside	16,0	16,0			mm
V _{ISOL}	ionation voitage	t = 1 second			4800			٧
1002		t = 1 minute	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA		4000			٧

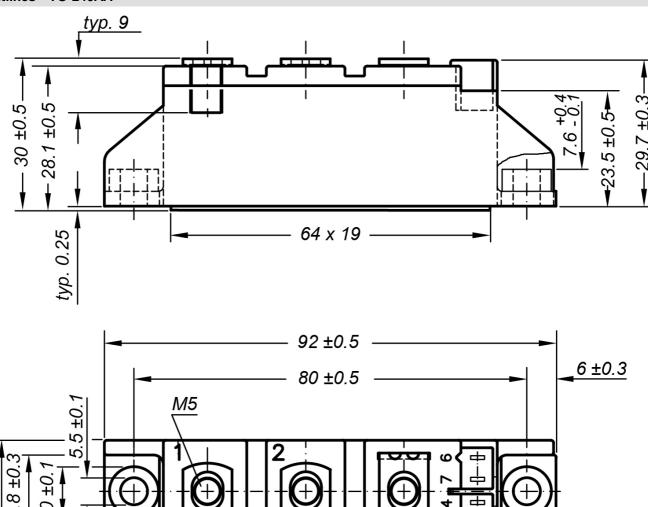


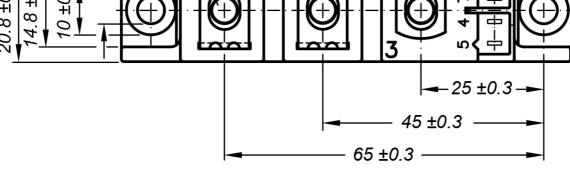
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MEK150-04DA	MEK150-04DA	Box	36	480086

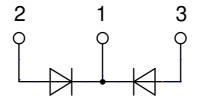
Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 150$ °C
$I \rightarrow V_0$)—[R ₀]	Fast Diode		
V _{0 max}	threshold voltage	0,73		V
R_{0max}	slope resistance *	1,3		mΩ



Outlines TO-240AA









Fast Diode

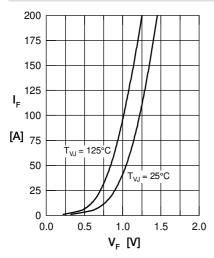


Fig. 1 Forward current I_F versus voltage drop V_F per leg